

## Effect of high Al<sub>2</sub>O<sub>3</sub> content on the microstructure and electrical properties of Co- and Ta-doped SnO<sub>2</sub> varistors

M. P. Torres Chiquito $^1 \cdot$  M. I. Pech-Canul $^2 \cdot$  M. B. Hernández $^3 \cdot$  L. V. García-Quiñonez $^4 \cdot$  M. Montoya Dávila $^1 \cdot$  J. A. Aguilar-Martínez $^5$ 

Received: 11 April 2019 / Accepted: 20 August 2019 © Springer Science+Business Media, LLC, part of Springer Nature 2019

## **Abstract**

Varistor behavior shows significant differences when the addition levels of different dopants like  $In_2O_3$ ,  $Cr_2O_3$ , and  $Al_2O_3$  are changed, thus stimulating current investigations on the  $SnO_2-Co_3O_4-Ta_2O_5$  ceramic system. In this contribution, the influence of high additions of  $Al_2O_3$  on the microstructure, structure and the electrical properties of  $SnO_2-Co_3O_4-Ta_2O_5$  varistors ([98.95-X]% $SnO_2-1$ %  $Co_3O_4-X$ %  $Al_2O_3-0.05$ %  $Ta_2O_5$ , where X=0, 0.05, 0.1, 1 or 2 mol%) is investigated. Characterization techniques such as thermal analysis, scanning electron microscopy and X-ray diffraction with Rietveld refinement were used for specimen analysis. The endothermic peaks in the ceramic system containing  $Al_2O_3$  additions between 0.05 and 1% are ascribed to the formation of the  $Co_2SnO_4$  and  $CoAl_2O_4$  spinel type phases. Doping the ceramic system with 1 and 2 mol%  $Al_2O_3$  leads to the formation of 1.163 and 3.449%, respectively, of the spinel phase  $Al_2CoO_4$ , which acts as a grain growth inhibitor because grain size decreases in about 16% for both addition levels. The apparent grains homogeneity and narrowest monomodal grain size distribution for the specimens with 2 mol%  $Al_2O_3$  confirm the inhibitory role. With the lowest level of  $Al_2O_3$  (0.05 mol%) the nonlinearity coefficient reaches a maximum, after which it decreases and fades at the highest alumina level. A remarkable decrease of about 50% in the leakage current from the reference specimen's value to that of the one with 0.05 mol%  $Al_2O_3$  concurrently with an increase in about 40% in the nonlinearity coefficient favors the potential use of alumina in the  $SnO_2-Co_3O_4-Ta_2O_5$  ceramic system.

- J. A. Aguilar-Martínez josue.aguilarmrt@uanl.edu.mx; josue.aguilar74@gmail.com
- Universidad Autónoma de Zacatecas, Maestría en Ciencia e ingeniería de los Materiales, UAZ, Av. Ramón López Velarde No. 801, 98000 Zacatecas, Zac., Mexico
- Centro de Investigación y de Estudios Avanzados del IPN-Unidad Saltillo, Av. Industria Metalúrgica 1062, Parque Industrial Saltillo-Ramos Arizpe, 25900 Ramos Arizpe, Coah., Mexico
- Tecnológico de Monterrey, Centro de Innovación y Diseño en Tecnología, Av. Eugenio Garza Sada 2501, 64849 Monterrey, NL, Mexico
- Centro de Investigación Científica y de Educación Superior de Ensenada, Baja California (CICESE); Alianza Centro No. 504, Parque de Investigación e Innovación Tecnológica (PIIT), Carretera Aeropuerto km. 10, 66629 Apodaca, NL, Mexico
- Universidad Autónoma de Nuevo León, Facultad de Ingeniería Mecánica y Eléctrica, Centro de Investigación e Innovación en Ingeniería Aeronáutica (CIIIA), Carretera a Salinas Victoria km. 2.3, 66600 Apodaca, NL, Mexico

Published online: 24 August 2019

## 1 Introduction

Since the introduction of zinc oxide (ZnO) as a large-non-linearity material by Matsuoka about 50 years ago [1], varistors have been the subject of a plethora of investigations. Varistors are electrical resistors whose response depend on the applied voltage. And albeit ZnO paved the way in varistor research and set the standard as a successful, profitable material, nowadays, a large number of ceramics, including TiO<sub>2</sub> [2], SrTiO<sub>3</sub> [3], WO<sub>3</sub> [4], CaCu<sub>3</sub>Ti<sub>4</sub>O<sub>12</sub> [5], BaTiO<sub>3</sub> [6] and SnO<sub>2</sub> [7] are currently under intense investigation.

For more than two decades, investigations on the use of aluminum oxide (Al<sub>2</sub>O<sub>3</sub>) in ceramic varistors have been conducted [8–12], and its effects as a dopant of a variety of ceramics including ZnO, WO<sub>3</sub>-based varistors, and ZPCCYA-based varistors have been related with the microstructure and electrical properties of the materials. However, most of the work done is reported on ZnO and using small amounts or low levels of Al<sub>2</sub>O<sub>3</sub> additions. Accordingly, in ZnO varistors it was observed that depending on the system and Al<sub>2</sub>O<sub>3</sub> additions, it may impact grain growth

